



Silicon Epitaxial Planar Transistor

TSA1036

FEATURES

- Large $I_{C,ICMAX.} = -600\text{mA}$.
- Low $V_{CE(sat)}$. Ideal for low-voltage operation.
- Complements the TSC2411.



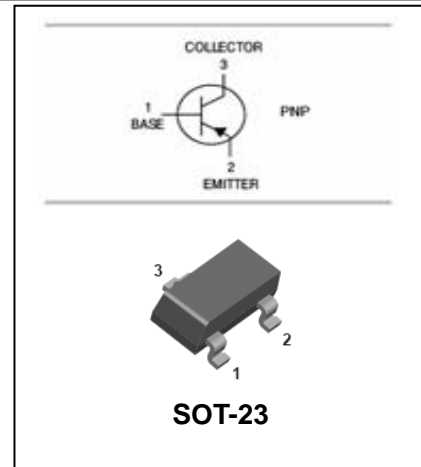
Lead-free

APPLICATIONS

- Epitaxial Planar Type.

ORDERING INFORMATION

Type No.	Marking	Package Code
TSA1036	RF•	SOT-23



MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-600	mA
P_C	Collector Dissipation	225	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	556	$^\circ\text{C}/\text{W}$
T_j	Operating Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-0.5V, I_C=0$			-50	nA
DC current gain	h_{FE}	$V_{CE}=-10V, I_C=-0.1mA$	75			
		$V_{CE}=-10V, I_C=-150mA$	100		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150mA, I_B=-15mA$			-0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-500mA, I_B=-50mA$			-1.3	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-50mA$ $f=100MHz$	200			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$ Z			8	pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Figure 1. DC Current Gain

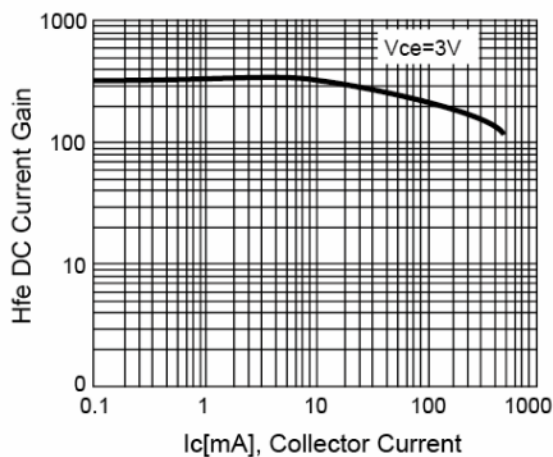
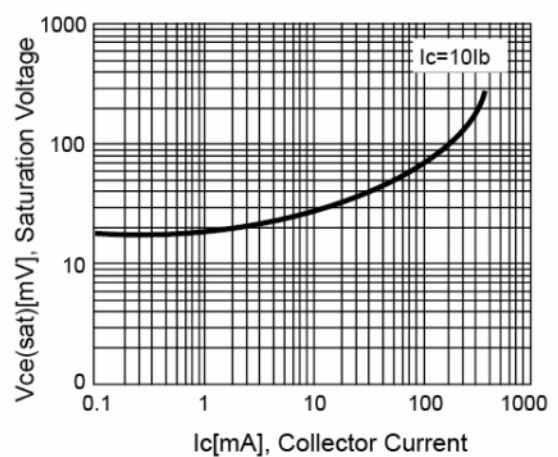


Figure 2. $V_{CE(SAT)}$ v.s. I_C





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Figure 3. $V_{BE(SAT)}$ v.s. I_c

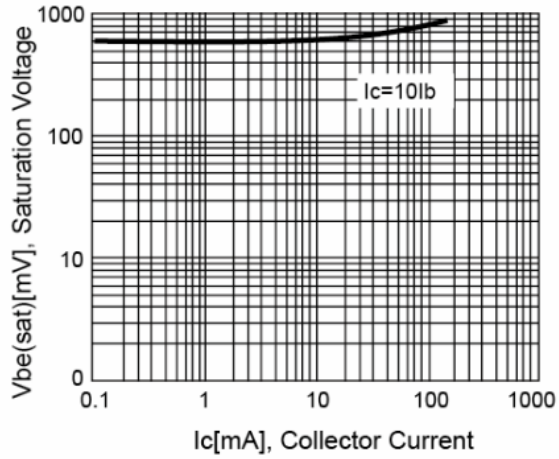


Figure 4. Cutoff Frequency vs. I_c

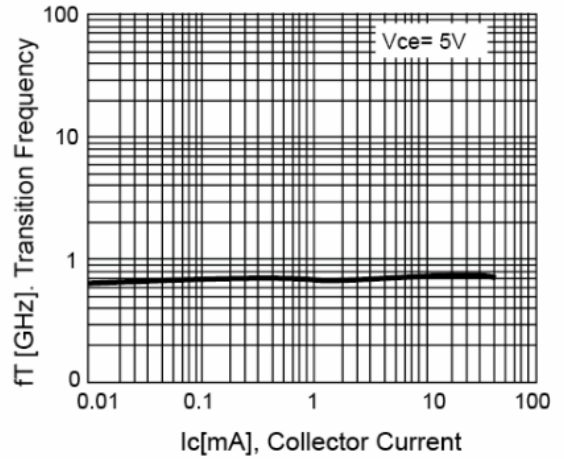
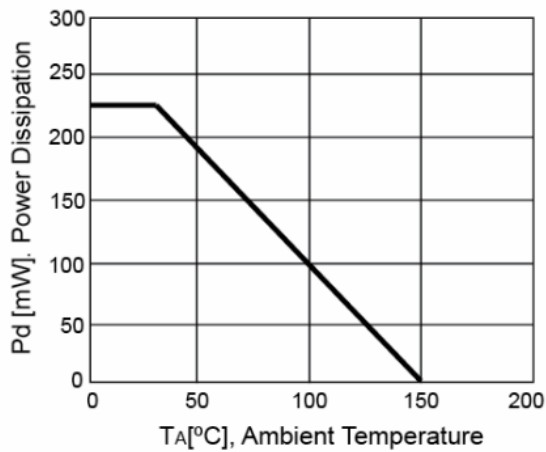


Figure 5. Power Derating Curve





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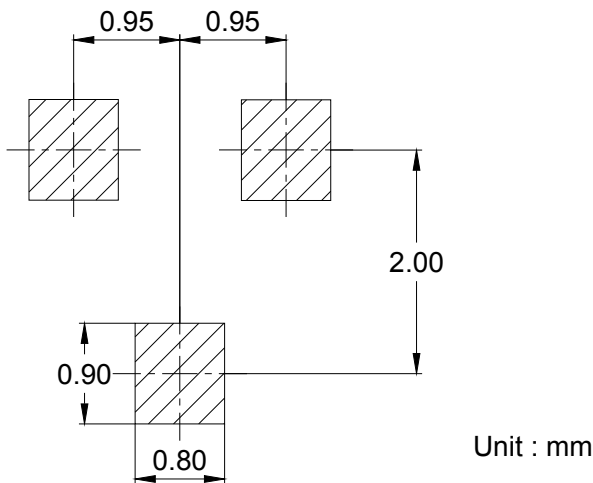
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23

SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
TSA1036	SOT-23	3000/Tape&Reel